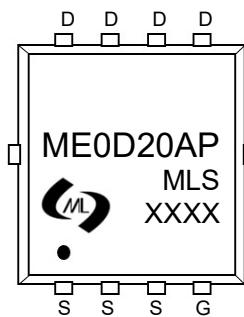


## Features

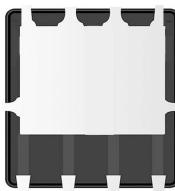
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

## Application

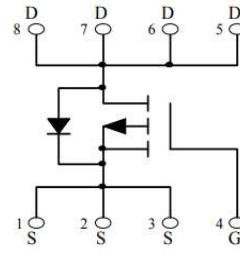
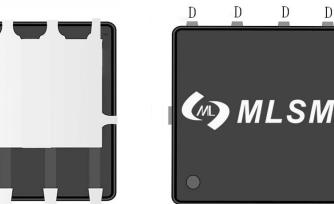
- Battery protection
- Load switch
- Power management



ME0D20AP: Device code  
XXXX : Code



PDFN3X3-8L view



Schematic diagram



Halogen-Free

Marking and pin assignment

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
<b>Common Ratings (TC=25°C Unless Otherwise Noted)</b>			
V <sub>DS</sub>	Drain-Source Breakdown Voltage	-30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
T <sub>J</sub>	Maximum Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature Range	-50 to 155	°C
I <sub>S</sub>	Diode Continuous Forward Current	Tc=25°C -20	A
<b>Mounted on Large Heat Sink</b>			
I <sub>DM</sub>	Pulse Drain Current Tested	Tc=25°C -80	A
I <sub>D</sub>	Continuous Drain Current	Tc=25°C -20	A
P <sub>D</sub>	Maximum Power Dissipation	Tc=25°C 5.3	W
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient	45	°C/W

## Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
ME0D20AP	PDFN3X3-8L	ME0D20AP	5,000	10,000	70,000	13"reel

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
BV <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	--	--	-1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	--	-2.5	V
R <sub>DS(on)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A	--	20	27	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	--	27	45	mΩ

**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)**

C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	--	1200	--	pF
C <sub>OSS</sub>	Output Capacitance		--	155	--	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance		--	140	--	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-15V, I <sub>D</sub> =-7A, V <sub>GS</sub> =-10V	--	52	--	nC
Q <sub>gs</sub>	Gate Source Charge		--	10	--	nC
Q <sub>gd</sub>	Gate Drain Charge		--	8.5	--	nC

**Switching Characteristics**

t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =-15V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω	--	13	--	nS
t <sub>r</sub>	Turn-on Rise Time		--	15	--	nS
t <sub>d(off)</sub>	Turn-Off Delay Time		--	200	--	nS
t <sub>f</sub>	Turn-Off Fall Time		--	100	--	nS

**Source- Drain Diode Characteristics**

V <sub>SD</sub>	Forward on voltage	T <sub>j</sub> =25°C, I <sub>s</sub> =-10A	--	--	-1.2	V
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### Typical Operating Characteristics

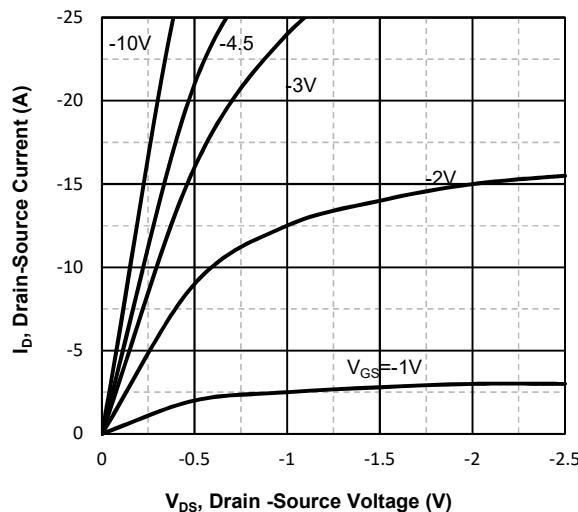


Fig1. Typical Output Characteristics

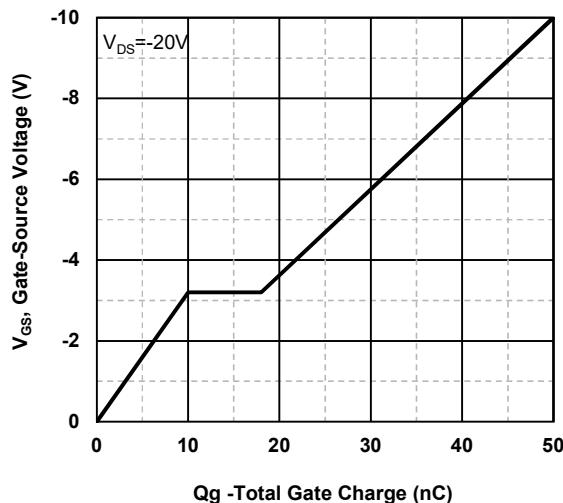


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

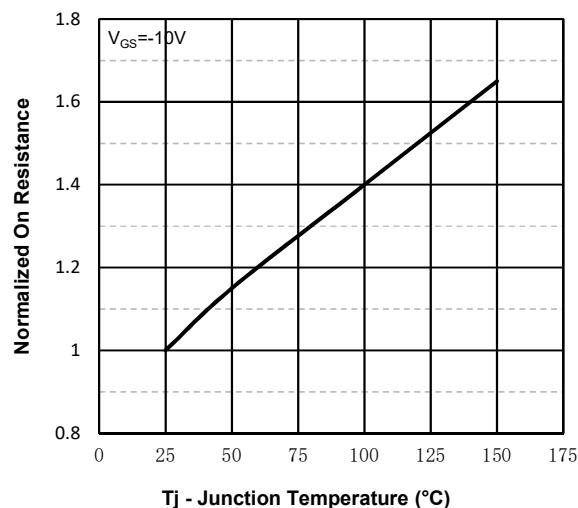


Fig3. Normalized On-Resistance Vs. Temperature

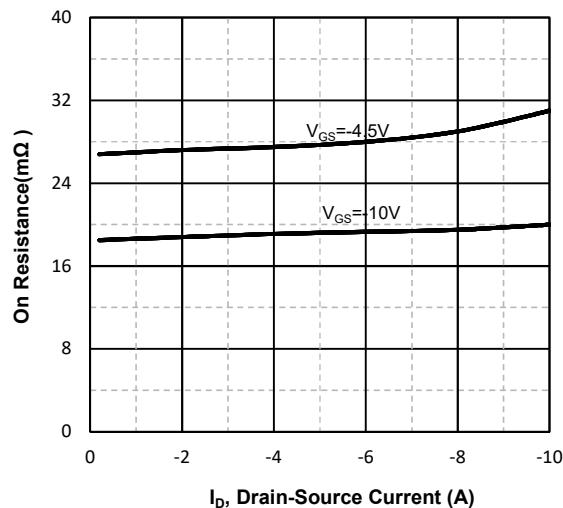


Fig4. On-Resistance Vs. Drain-Source Current

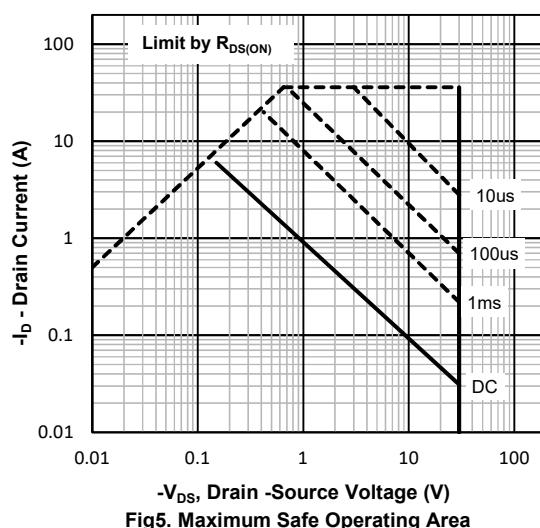


Fig5. Maximum Safe Operating Area

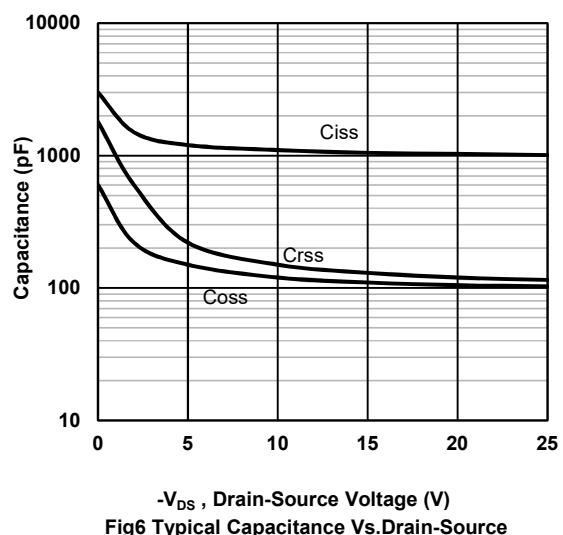
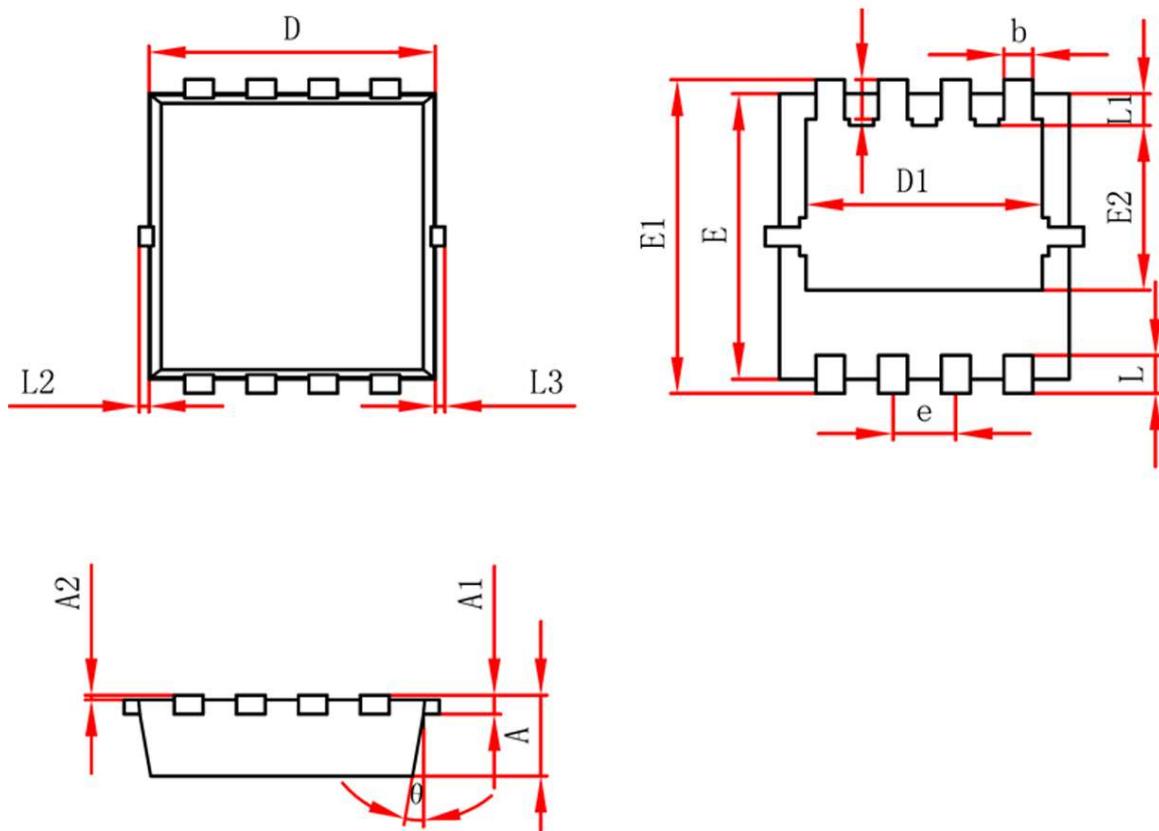


Fig6 Typical Capacitance Vs.Drain-Source

## PDFN3X3-8L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.750	0.850	0.030	0.034
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.950	3.150	0.117	0.125
D1	2.400	2.500	0.095	0.099
E	2.950	3.050	0.117	0.121
E1	3.250	3.350	0.129	0.132
E2	1.685	1.785	0.067	0.071
b	0.250	0.350	0.010	0.014
e	0.600	0.700	0.024	0.028
L	0.350	0.450	0.014	0.018
L1	0.325	0.425	0.013	0.017
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.365	0.465	0.014	0.018
$\theta$	10°	12°	10°	12°